ECH8695R

Power MOSFET
for 1-2 Cells Lithium-ion Battery Protection
24 V, 9.1 mΩ, 11 A, Dual N-Channel

ON Semiconductor®

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This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-2 cells Lithium-ion Battery applications.

Features

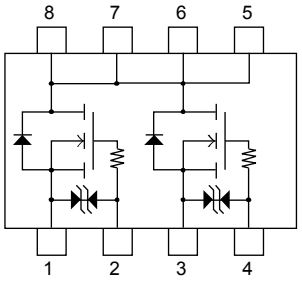
- Low On-Resistance
- 2.5 V drive
- Common-Drain Type
- ESD Diode-Protected Gate
- Built-in Gate Protection Resistor
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- 1-2 cells Lithium-ion Battery Charging and Discharging Switch

V_{DSS}	R_{DS}(on) Max	I_D Max
24 V	9.1 mΩ @ 4.5 V	11 A
	9.5 mΩ @ 4.0 V	
	11.5 mΩ @ 3.1 V	
	13.3 mΩ @ 2.5 V	

ELECTRICAL CONNECTION
N-Channel



1 : Source1
2 : Gate1
3 : Source2
4 : Gate2
5 : Drain
6 : Drain
7 : Drain
8 : Drain

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

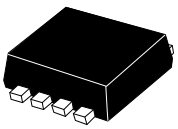
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	24	V
Gate to Source Voltage	V_{GSS}	±12.5	V
Drain Current (DC)	I_D	11	A
Drain Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I_{DP}	60	A
Power Dissipation Surface mounted on ceramic substrate (900 mm^2 × 0.8 mm) 1 unit	P_D	1.4	W
Total Dissipation Surface mounted on ceramic substrate (900 mm^2 × 0.8 mm)	P_T	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55 to +150	°C

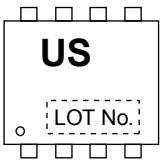
Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient Surface mounted on ceramic substrate (900 mm^2 × 0.8 mm) 1 unit	$R_{\theta JA}$	89.2	°C/W

MARKING





SOT-28FL / ECH8

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 1 mA, V_{GS} = 0 V	24			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±8 V, V_{DS} = 0 V			±1	μA
Gate Threshold Voltage	$V_{GS}(th)$	V_{DS} = 10 V, I_D = 1 mA	0.5		1.3	V
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 5 A		6.5		S
Static Drain to Source On-State Resistance	$R_{DS}(on)$	I_D = 5 A, V_{GS} = 4.5 V	5.6	7.0	9.1	mΩ
		I_D = 5 A, V_{GS} = 4.0 V	5.8	7.3	9.5	mΩ
		I_D = 5 A, V_{GS} = 3.1 V	6.5	8.2	11.5	mΩ
		I_D = 2.5 A, V_{GS} = 2.5 V	7.6	9.5	13.3	mΩ
Turn-ON Delay Time	$t_d(on)$	See Fig. 1 (Note 3)		300		ns
Rise Time	t_r			320		ns
Turn-OFF Delay Time	$t_d(off)$			19.7		μs
Fall Time	t_f			22.3		μs
Turn-ON Delay Time	$t_d(on)$	See Fig. 2 (Note 3)		300		ns
Rise Time	t_r			320		ns
Turn-OFF Delay Time	$t_d(off)$			1,240		μs
Fall Time	t_f			370		μs
Total Gate Charge	Qg	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 11 A		10		nC
Gate to Source Charge	Qgs			1.6		nC
Gate to Drain “Miller” Charge	Qgd			1.5		nC
Forward Diode Voltage	V_{SD}	I_S = 11 A, V_{GS} = 0 V		0.77	1.2	V

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Note 3 : The fall switching time is dependent on the input pulse width.

Fig.1 Switching Time Test Circuit 1

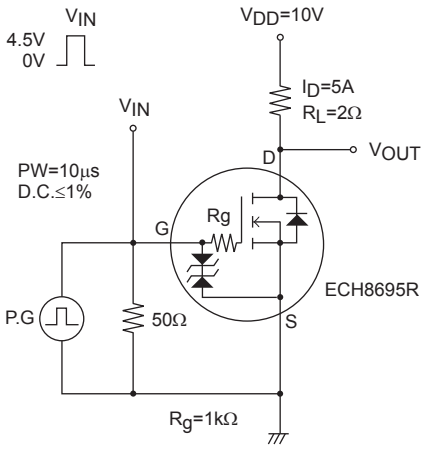
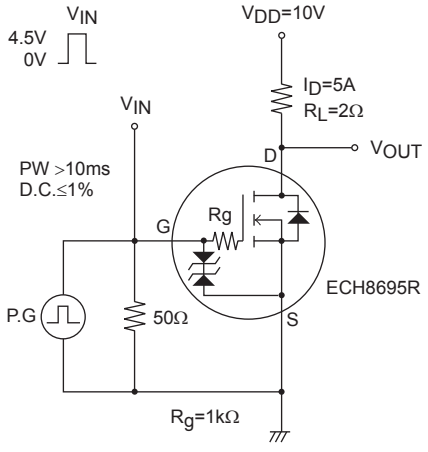
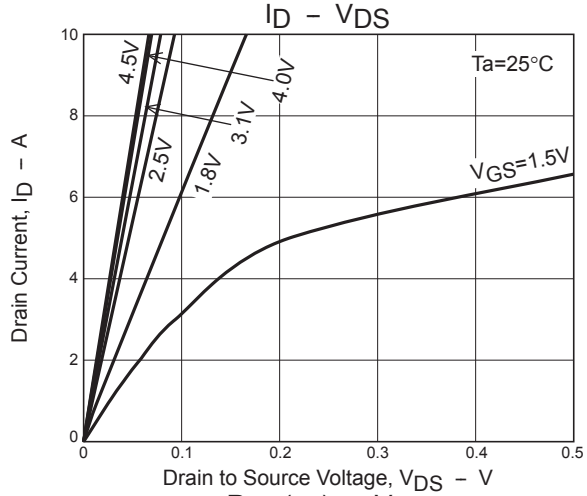
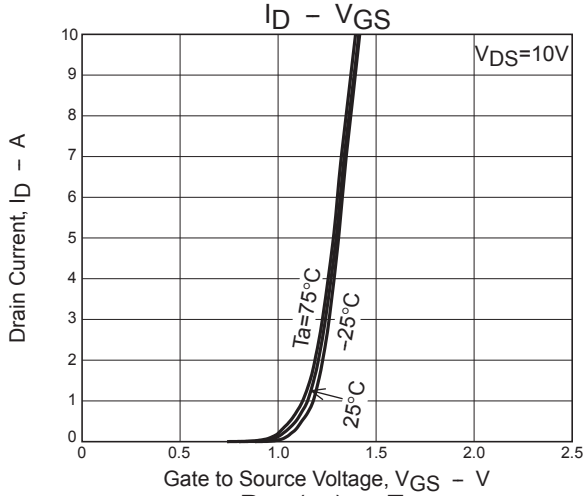
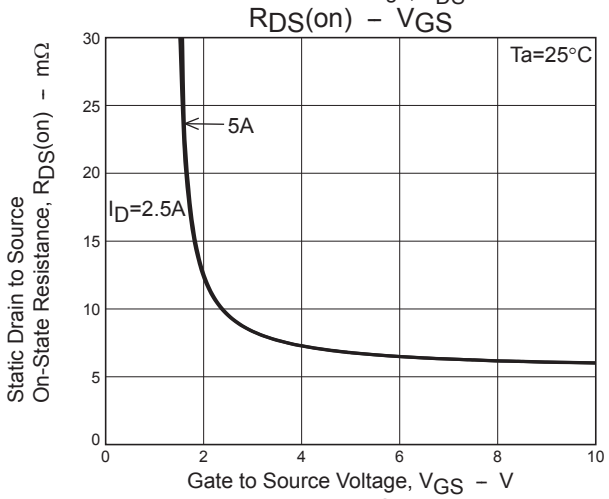


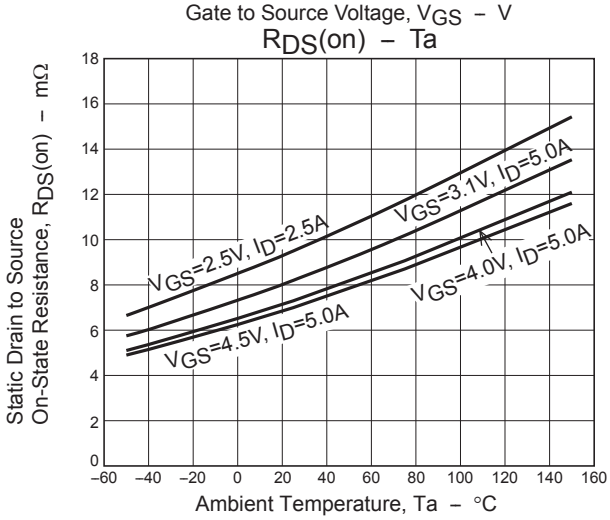
Fig.2 Switching Time Test Circuit 2

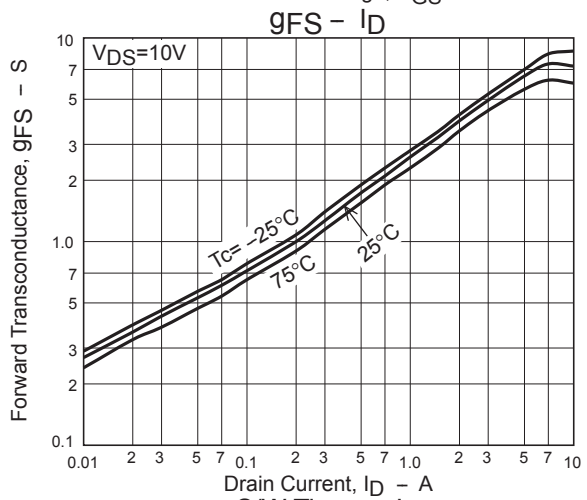


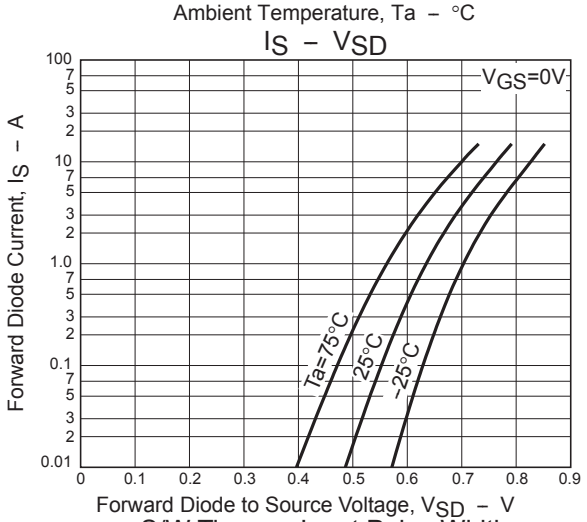

ID – VDS
Ta=25°C
4.5V
4.0V
3.1V
2.5V
1.8V
VGS=1.5V
Drain Current, ID – A
Drain to Source Voltage, VDS – V

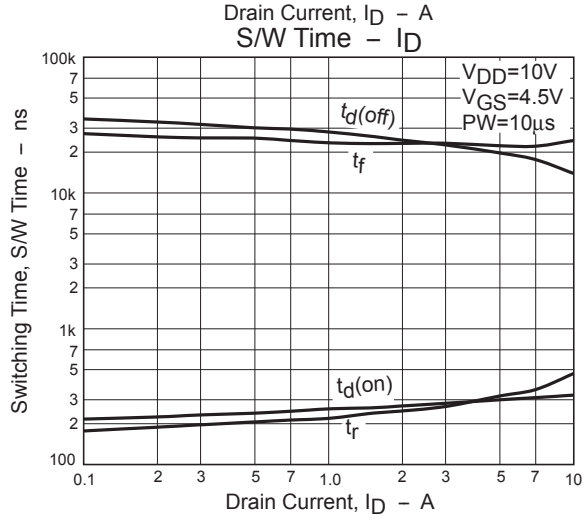

ID – VGS
VDS=10V
Ta=75°C
–25°C
25°C
Drain Current, ID – A
Gate to Source Voltage, VGS – V

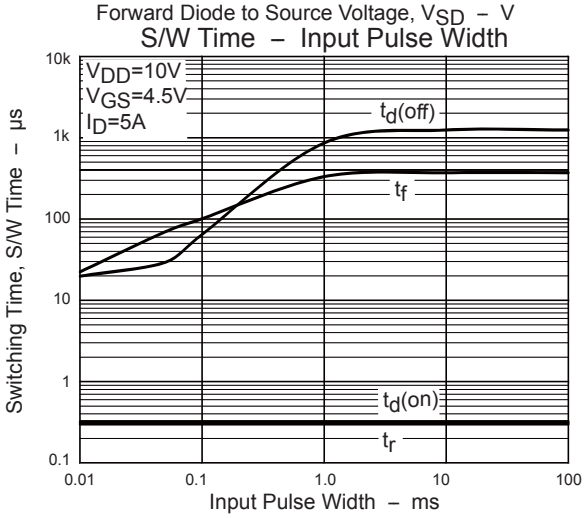

RDS(on) – VGS
Ta=25°C
5A
ID=2.5A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Gate to Source Voltage, VGS – V

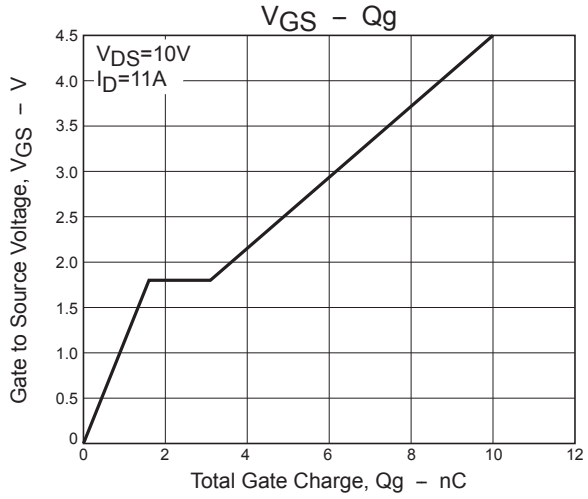

RDS(on) – Ta
VGS=2.5V, ID=2.5A
VGS=3.1V, ID=5.0A
VGS=4.0V, ID=5.0A
VGS=4.5V, ID=5.0A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C

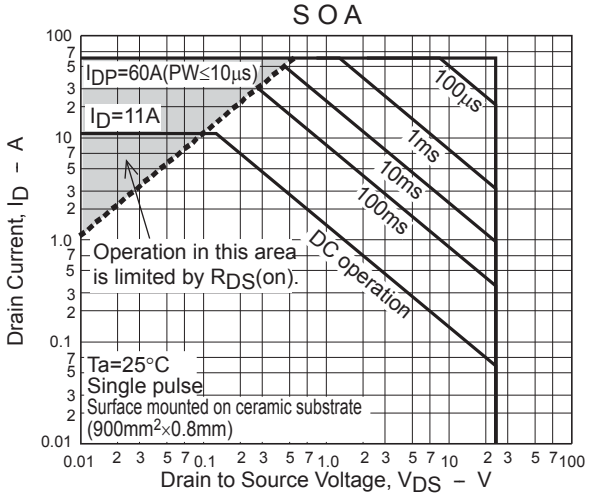

gFS – ID
VDS=10V
Tc= –25°C
75°C
25°C
Forward Transconductance, gFS – S
Drain Current, ID – A

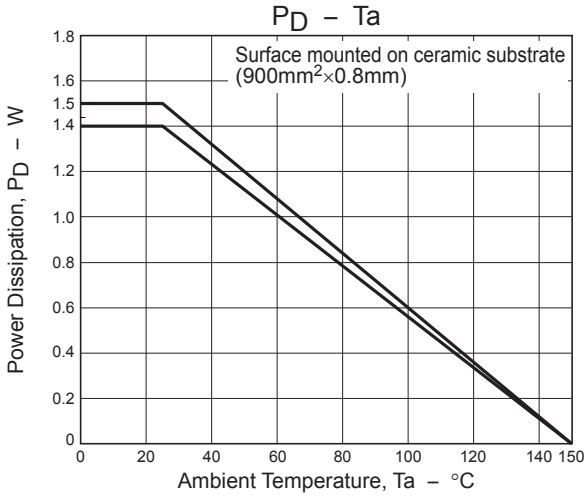

IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Forward Diode Current, IS – A
Forward Diode to Source Voltage, VSD – V

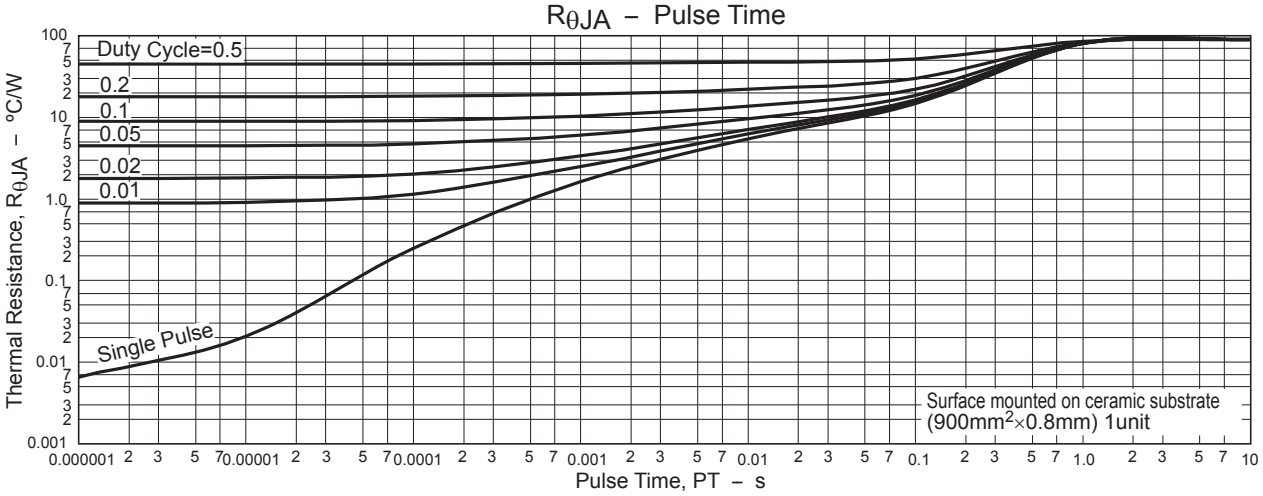

S/W Time – ID
VDD=10V
VGS=4.5V
PW=10µs
td(off)
tf
td(on)
tr
Switching Time, S/W Time – ns
Drain Current, ID – A


S/W Time – Input Pulse Width
VDD=10V
VGS=4.5V
ID=5A
td(off)
tf
td(on)
tr
Switching Time, S/W Time – µs
Input Pulse Width – ms


VGS – Qg
VDS=10V
ID=11A
Gate to Source Voltage, VGS – V
Total Gate Charge, Qg – nC


S O A
IDP=60A(PW≤10μs)
ID=11A
100μs
1ms
10ms
100ms
DC operation
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
Surface mounted on ceramic substrate
(900mm2×0.8mm)
Drain Current, ID – A
Drain to Source Voltage, VDS – V

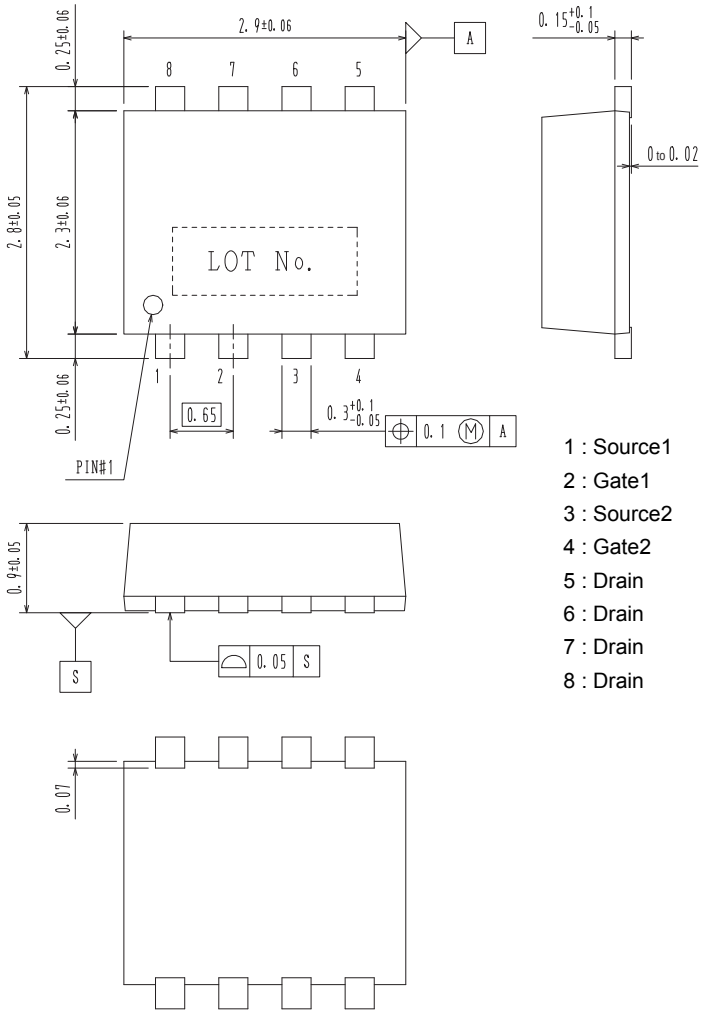

PD – Ta
Surface mounted on ceramic substrate
(900mm2×0.8mm)
Power Dissipation, PD – W
Ambient Temperature, Ta – °C


RθJA – Pulse Time
Duty Cycle=0.5
0.2
0.1
0.05
0.02
0.01
Single Pulse
Surface mounted on ceramic substrate
(900mm2×0.8mm) 1unit
Thermal Resistance, RθJA – °C/W
Pulse Time, PT – s

PACKAGE DIMENSIONS

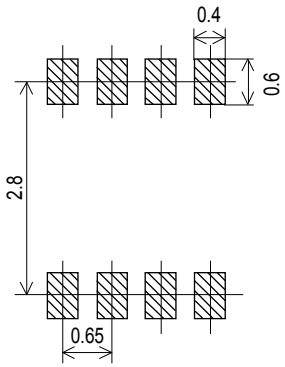
unit : mm

SOT-28FL / ECH8
CASE 318BF
ISSUE O



1 : Source1
2 : Gate1
3 : Source2
4 : Gate2
5 : Drain
6 : Drain
7 : Drain
8 : Drain

Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
ECH8695R-TL-W	US	SOT-28FL / ECH8 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the ECH8695R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects. Please contact sales for use except the designated application.